

Please replace the Abstract with the following amended Abstract:

Abstract of the Disclosure

~~Semiconductor component comprising an integrated latticed capacitance structure.~~

An insulating layer which is produced on a semiconductor substrate has a capacitance structure (K) produced in it. The capacitance structure (K) has at least one first substructure (T1a) which has a metal latticed region (~~G1a to G1e~~) and electrically conductive regions (~~P1a to P1e~~) which are arranged in the cutouts in the metal latticed region (~~G1a to G1e~~), the metal latticed region (~~G1a to G1e~~) ~~being~~ are electrically connected to a first connecting line, and the electrically conductive regions (~~P1a to P1e~~) ~~being~~ are electrically connected to a second connecting line.

A clean version of the amended Abstract is provided in the attached sheet.